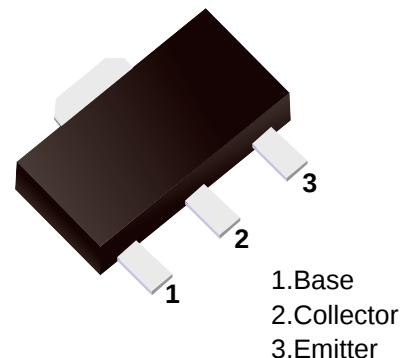


PNP Transistors

■ Features

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-50	V
Collector - Emitter Voltage	V _{CE0}	-50	
Emitter - Base Voltage	V _{EB0}	-6	
Collector Current - Continuous	I _C	-2	A
Collector Current - Pulse	I _{CM}	-3	
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

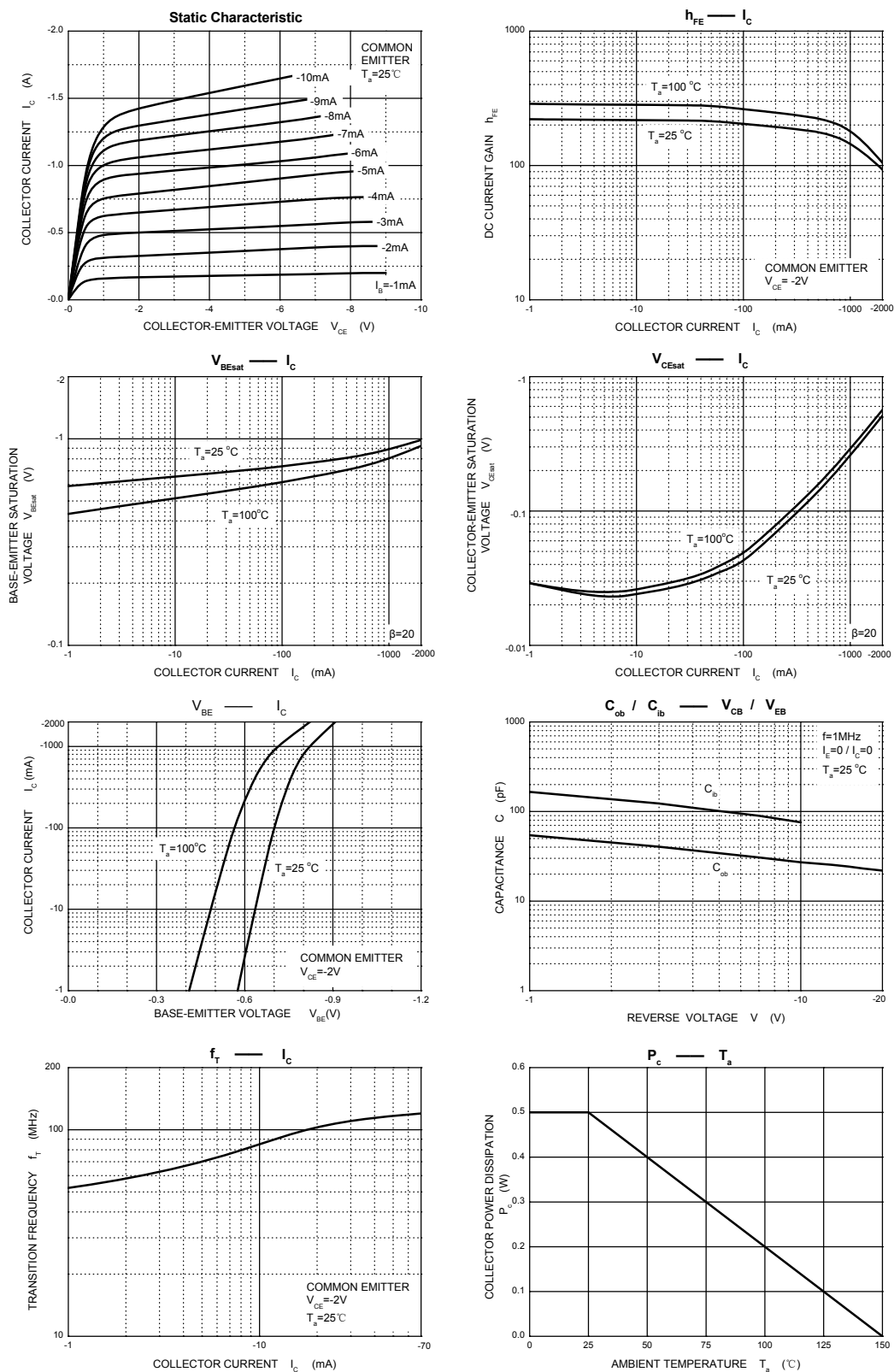
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -50 μA, I _E =0	-50			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B =0	-50			
Emitter - base breakdown voltage	V _{EB0}	I _E = -50 μA, I _C =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50 V, I _E =0			-100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-50mA			-0.35	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-1A, I _B =-50mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -500mA	82		270	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0,f=1MHz		36		pF
Transition frequency	f _T	V _{CE} = -2V, I _C = -500mA,f=100MHz		200		MHz

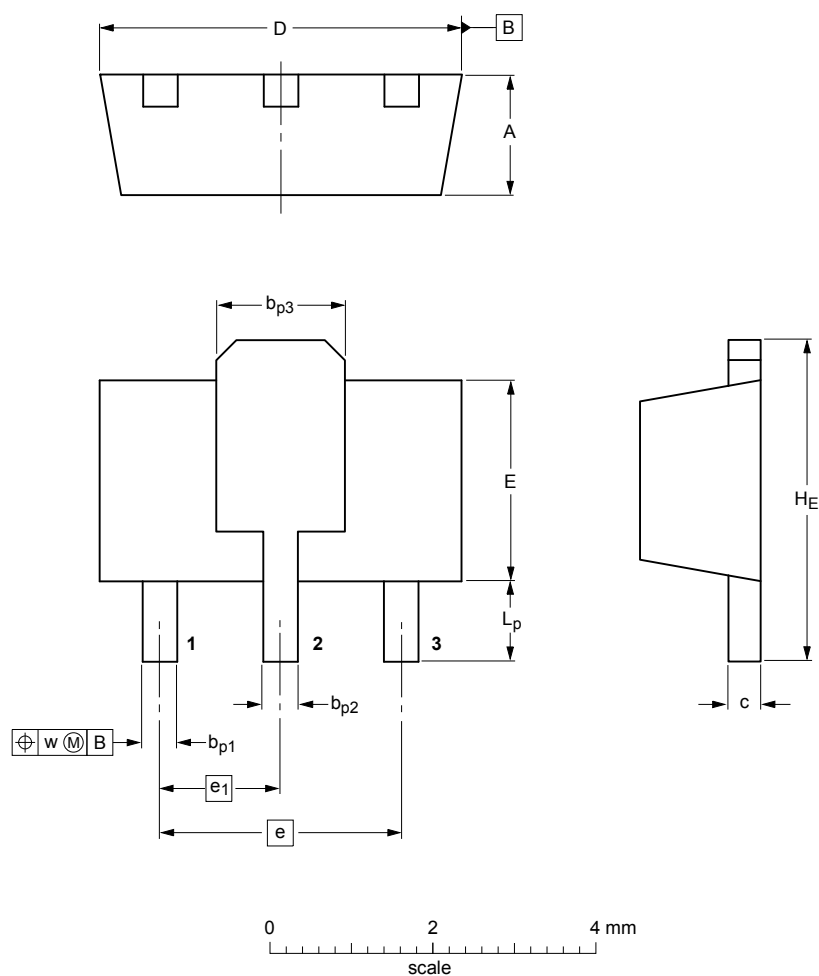
■ Classification of h_{FE}

Type	2SA1797-P	2SA1797-Q
Range	82-180	120-270
Marking	AGP	AGQ

■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13